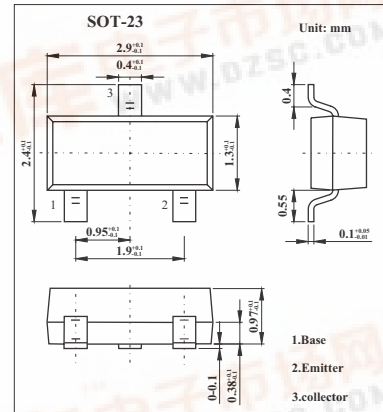


SMD Type Transistors

Silicon PNP Epitaxial  
2SA1298

Features

- High DC current gain:  $hFE = 100 \sim 320$
- Low saturation voltage:  $V_{CE(sat)} = -0.4V(max)$   
( $I_C = -500 mA, I_B = -20 mA$ )
- Suitable for driver stage of small motor
- Small package



Absolute Maximum Ratings  $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	-30	V
Collector-emitter voltage	$V_{CE0}$	-25	V
Emitter-base voltage	$V_{EB0}$	-5	V
Collector current	$I_C$	-800	mA
Base current	$I_B$	-160	mA
Collector power dissipation	$P_C$	200	mW
Junction temperature	$T_j$	150	$^\circ C$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ C$

Electrical Characteristics  $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cut-off current	$I_{CBO}$	$V_{CB} = -30 V, I_E = 0$			-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -50 V, I_C = 0$			-0.1	$\mu A$
Collector-emitter breakdown voltage	$V_{(BR) CE0}$	$I_C = -10 mA, I_B = 0$	-25			V
Emitter-base breakdown voltage	$V_{(BR) EBO}$	$I_E = -0.1 mA, I_C = 0$	-5			V
DC current gain	$hFE$	$V_{CE} = -1 V, I_C = -100 mA$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500 mA, I_B = -20 mA$			-0.4	V
Base-emitter voltage	$V_{BE}$	$V_{CE} = -1 V, I_C = -10 mA$	-0.5		-0.8	V
Transition frequency	$f_T$	$V_{CE} = -5 V, I_C = -10 mA$		120		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10 V, I_E = 0, f = 1 MHz$		13		pF

hFE Classification

Marking	IO	IY
hFE	100~200	160~320

